TinyLogic UHS Dual Buffer with 3-STATE Outputs

NC7WZ126

Description

The NC7WZ126 is a Dual Non–Inverting Buffer with independent active HIGH enables for the 3–STATE outputs. The Ultra High Speed device is fabricated with advanced CMOS technology to achieve superior switching performance with high output drive while maintaining low static power dissipation over a broad V_{CC} operating range. The device is specified to operate over the 1.65 V to 5.5 V V_{CC} operating range. The inputs and outputs are high impedance when V_{CC} is 0 V. Inputs tolerate voltages up to 5.5 V independent of V_{CC} operating range. Outputs tolerate voltages above V_{CC} when in the 3–STATE condition.

Features

- Space Saving US8 Surface Mount Package
- MicroPak[™] Pb-Free Leadless Package
- Ultra High Speed: t_{PD} 2.6 ns Typ. into 50 pF at 5 V V_{CC}
- High Output Drive: ±24 mA at 3 V V_{CC}
- Broad V_{CC} Operating Range: 1.65 V to 5.5 V
- Matches the Performance of LCX when Operated at 3.3 V V_{CC}
- Power Down High Impedance Inputs / Outputs
- Overvoltage Tolerant Inputs Facilitate 5 V to 3 V Translation
- Outputs are Overvoltage Tolerant in 3-STATE Mode
- Patented Noise / EMI Reduction Circuitry Implemented
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

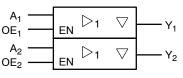
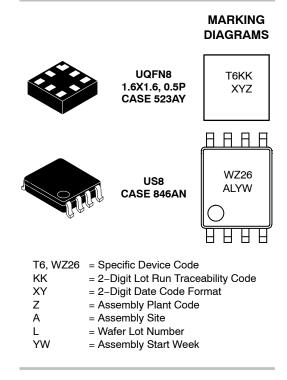


Figure 1. Logic Symbol



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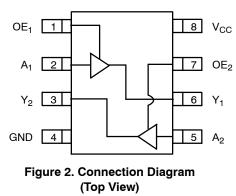
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ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

Connection Diagrams



PIN DESCRIPTIONS

Pin Names	Description
OE _n	Enable Inputs for 3-STATE Outputs
A _n	Inputs
Y _n	3-STATE Outputs

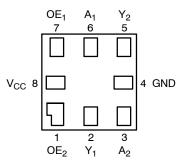


Figure 3. Pad Assignments for MicroPak (Top Thru View)

FUNCTION TABLE

Inp	Inputs		
OE	A _n	Y _n	
Н	L	L	
Н	н	Н	
L	L	Z	
L	Н	Z	

H = HIGH Logic Level L = LOW Logic Level Z = 3-STATE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parame	Min	Мах	Unit	
V _{CC}	Supply Voltage		-0.5	6.5	V
V _{IN}	DC Input Voltage (Note 1)		-0.5	6.5	V
V _{OUT}	DC Output Voltage		-0.5	6.5	V
Ι _{ΙΚ}	DC Input Diode Current	V _{IN} < 0 V	-	-50	mA
Ι _{ΟΚ}	DC Output Diode Current	V _{OUT} < 0 V	-	-50	mA
I _{OUT}	DC Output Source / Sink Current		-	±50	mA
I _{CC} / I _{GND}	DC V _{CC} / GND Current		-	±100	mA
T _{STG}	Storage Temperature Range		-65	+150	°C
TJ	Junction Temperature under Bias	_	+150	°C	
ΤL	Junction Lead Temperature (Solde	_	+260	°C	
P _D	Power Dissipation in Still Air	US8 MicroPak-8		500 539	mW

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The input and output negative voltage ratings may be exceeded is the input and output diode current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

Symbol		Parameter	Min	Max	Unit
V _{CC}	Supply Voltage Operating		1.65	5.5	V
	Supply Voltage Data Rete	ntion	1.5	5.5	
V _{IN}	Input Voltage		0	5.5	V
V _{OUT}	Output Voltage	Active State	0	V _{CC}	V
		3-State	0	5.5	V
T _A	Operating Temperature		-40	+85	°C
t _r , t _f	Input Rise and Fall Time	V_{CC} = 1.8 V ±0.15 V, 2.5 V ±0.2 V	0	20	ns/V
		$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	0	10	
		$V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	5	
θ_{JA}	Thermal Resistance	US8 MicroPak–8		250 232	°C/W

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.Unused inputs must be held HIGH or LOW. They may not float.

DC ELECTICAL CHARACTERISTICS

			T _A = +25°C			T _A = −40 to +85°C							
Symbol	Parameter	Conc	litions	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit			
V _{IH}	HIGH Level Input			1.65 to 1.95	0.65 V _{CC}	-	-	0.65 V _{CC}	_	V			
	Voltage			2.3 to 5.5	0.7 V _{CC}	-	-	0.7 V _{CC}	_				
VIL	LOW Level Input			1.65 to 1.95	-	-	0.35 V _{CC}	-	0.35 V _{CC}	V			
	Voltage			2.3 to 5.5	-	-	0.3 V _{CC}	_	0.3 V _{CC}				
V _{OH}	HIGH Level Output	$V_{IN} = V_{IH}$ or	I _{OH} = -100 μA	1.65	1.55	1.65	-	1.55	-	V			
	Voltage	VIL		2.3	2.2	2.3	-	2.2	-				
				3.0	2.9	3.0	-	2.9	-				
				4.5	4.4	4.5	-	4.4	-				
		$V_{IN} = V_{IH}$ or	I _{OH} = -4 mA	1.65	1.29	1.52	-	1.29	-				
		V _{IL}	I _{OH} = -8 mA	2.3	1.9	2.15	-	1.9	-				
			I _{OH} = -16 mA	3.0	2.4	2.80	-	2.4	-				
						I _{OH} = -24 mA	3.0	2.3	2.68	-	2.3	-	
			I _{OH} = -32 mA	4.5	3.8	4.20	-	3.8	-				
V _{OL}			$V_{IN} = V_{IH}$ or	I _{OL} = 100 μA	1.65	-	0.0	0.10	-	0.10	V		
	Voltage	V _{IL}		2.3	-	0.0	0.10	-	0.10				
				3.0	-	0.0	0.10	-	0.10				
				4.5	-	0.0	0.10	-	0.10				
		$V_{IN} = V_{IH}$ or	I _{OL} = 4 mA	1.65	-	0.08	0.24	-	0.24				
		V _{IL}	I _{OL} = 8 mA	2.3	-	0.10	0.3	-	0.3				
			I _{OL} = 16 mA	3.0	-	0.15	0.4	-	0.4				
			I _{OL} = 24 mA	3.0	-	0.22	0.55	-	0.55				
			I _{OL} = 32 mA	4.5	-	0.22	0.55	-	0.55				
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V, G	ND	1.65 to 5.5	_	-	±0.1	_	±1	μA			
I _{OZ}	3–STATE Output Leakage	$V_{IN} = V_{IH} \text{ or } V_{I}$ $0 \le V_{OUT} \le 5.5$	L S V	1.65 to 5.5	_	-	±0.5	_	±5	μA			
I _{OFF}	Power Off Leakage Current	V_{IN} or V_{OUT} = 5.5 V		0.0	_	-	1	_	10	μA			
I _{CC}	Quiescent Supply Current	V _{IN} = 5.5 V, GI	ND	1.65 to 5.5	-	-	1	-	10	μA			

NOISE CHARACTERISTICS

				T _A = +25°C		
Symbol	Parameter	Conditions	V _{CC} (V)	Тур	Max	Unit
V _{OLP} (Note 3)	Quiet Output Maximum Dynamic V _{OL}	C _L = 50 pF	5.0	-	1.0	V
V _{OLV} (Note 3)	Quiet Output Minimum Dynamic V _{OL}	C _L = 50 pF	5.0	-	1.0	V
V _{OHV} (Note 3)	Quiet Output Minimum Dynamic V _{OH}	C _L = 50 pF	5.0	-	4.0	V
V _{IHD} (Note 3)	Minimum HIGH Level Dynamic Input Voltage	C _L = 50 pF	5.0	-	3.5	V
V _{ILD} (Note 3)	Maximum LOW Level Dynamic Input Voltage	C _L = 50 pF	5.0	-	1.5	V

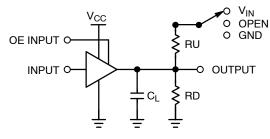
3. Parameter guaranteed by design.

AC ELECTRICAL CHARACTERISTICS

					T _A = +25°C	;	T _A = -40	to +85°C		
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit	
t _{PLH}	Propagation Delay	$C_L = 15 pF$	1.8 ±0.15	_	-	12.0	-	13.0	ns	
t _{PHL}	A _n to Yn (Figure 4, 6)	$RD = 1 M\Omega$ $S_1 = OPEN$	2.5 ±0.2	_	-	7.5	-	8.0		
			3.3 ±0.3	-	-	5.2	-	5.5		
			5.0 ±0.5	-	-	4.5	-	4.8		
		$C_L = 50 \text{ pF},$	3.3 ±0.3	-	-	5.7	-	6.0		
		$RD = 500 \Omega$ $S_1 = OPEN$	5.0 ±0.5	-	-	5.0	-	5.3		
toslh	Output to Output Skew	$C_L = 50 \text{ pF},$	3.3 ±0.3	-	-	1.0	-	1.0	ns	
toshl	(Note 4) (Figure 4, 6)	$RD = 500 \Omega$ $S_1 = OPEN$	5.0 ±0.5	-	-	0.8	-	0.8		
t _{PZL}	$\begin{array}{c} \text{Output Enable Time} \\ (\text{Figure 4, 6}) \end{array} \qquad \begin{array}{c} \text{C}_{L} = 50 \text{ pF} \\ \text{RD,RU} = 500 \ \Omega \\ \text{S}_{1} = \text{GND for } \text{t}_{\text{PZH}} \\ \text{S}_{1} = \text{V}_{I} \text{ for } \text{t}_{\text{PZL}} \\ \text{V}_{I} = 2 \text{ x } \text{V}_{\text{CC}} \end{array}$			-	15.0	ns				
t _{PZH}		2.5 ±0.2	_	-	8.5	-	9.0			
		3.3 ±0.3	_	-	6.2	-	6.5			
				5.0 ±0.5	-	-	5.5	-	5.8	
t _{PLZ}	Output Disable Time	$C_L = 50 \text{ pF}$	1.8 ±0.15	_	-	12.0	-	13.0	ns	
t _{PHZ}	(Figure 4, 6)	RD,RU = 500 Ω S ₁ = GND for t _{PZH}	2.5 ±0.2	_	-	8.0	-	8.5		
	S ₁ = V _I for t _{PZL} V _I = 2 x V _{CC}	$\begin{array}{c} S_1 = V_1 \text{ for } t_{PZL} \\ V_1 = 2 \times V_{CC} \end{array} 3.3 \pm 0.3 - \end{array}$	$S_1 = V_1$ for t_{PZL} $V_1 = 2 \times V_{CC}$	_	-	5.7	-	6.0		
			5.0 ±0.5	-	-	4.7	-	5.0		
C _{IN}	Input Capacitance		0	I	2.5	-	-	-	pF	
C _{OUT}	Output Capacitance		5.0	-	4	-	-	_	pF	
C _{PD}	Power Dissipation Capacitance (Figure 5)	(Note 5)	3.3	-	10	-	-	-	pF	
	Capacitance (Figure 5)		5.0	-	12	-	-	-		

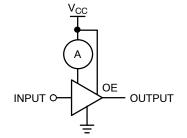
4. Parameter guaranteed by design. t_{OSLH} = |t_{PLHmax} - t_{PLHmin}|; t_{OSHL} = |t_{PHLmax} - t_{PHLmin}|.
5. C_{PD} is defined as the value of the internal equivalent capacitance which is derived from dynamic operating current consumption (I_{CCD}) at no output loading and operating at 50% duty cycle. (see Figure 5) C_{PD} is related to I_{CCD} dynamic operating current by the expression: I_{CCD} = (CPD) (V_{CC}) (f_{IN}) + (I_{CC}static).

AC Loading and Waveforms



 C_L includes load and stray capacitance Input PRR = 1.0 MHz; t_W = 500 ns

Figure 4. AC Test Circuit



Input = AC Waveform; $t_r = t_f = 1.8$ ns; PRR = 10 MHz; Duty Cycle = 50%.

Figure 5. I_{CCD} Test Circuit

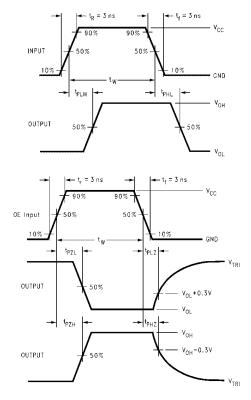


Figure 6. AC Waveforms

ORDERING INFORMATION

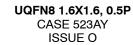
Order Number	Top Mark	Package	Shipping [†]
NC7WZ126K8X	WZ26	8-Lead US8, JEDEC MO-187, Variation CA 3.1 mm Wide	3000 / Tape & Reel
NC7WZ126L8X	T6	8–Lead MicroPak, 1.6 mm Wide (Pb–Free)	5000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

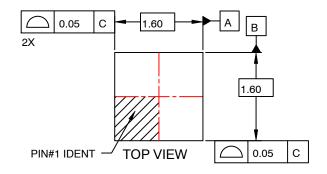
6. Pb-Free package per JEDEC J-STD-020B.

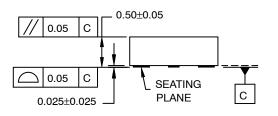
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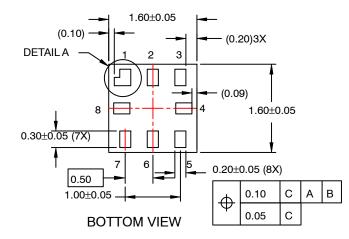


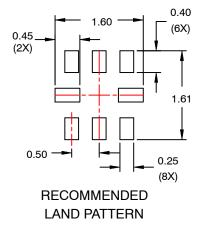
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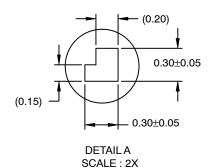
SIDE VIEW





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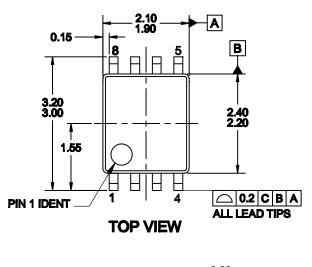
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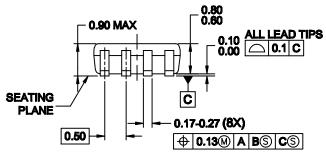
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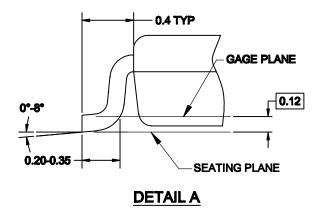
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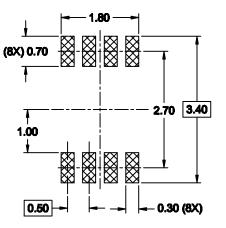
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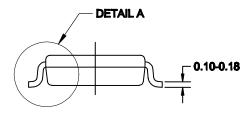




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